查询BYV25F-600体 **BYV25F-600**

Enhanced ultrafast power diode Rev. 1 — 1 October 2010

Product data sheet

Product profile 1.

1.1 General description

Enhanced ultrafast power diode in a SOD59 (2-lead TO-220AC) plastic package.

1.2 Features and benefits

- High thermal cycling performance
- Low on-state losses

1.3 Applications

- Dual Mode (DCM and CCM) PFC
- Low thermal resistance
- Soft recovery characteristic
- Power Factor Correction (PFC) for Interleaved Topology

1.4 Quick reference data

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
V _{RRM}	repetitive peak reverse voltage		-	-	600	V
I _{F(AV)}	average forward current	square-wave pulse; $\delta = 0.5$; T _{mb} ≤ 126 °C; see <u>Figure 1</u> ; see <u>Figure 2</u>	-	-71	5	A
Static cha	racteristics					
V _F	forward voltage	I _F = 5 A; T _j = 25 °C; see <u>Figure 5</u>	E WW	1.3	1.9	V
		I _F = 5 A; T _j = 150 °C; see <u>Figure 5</u>	-	1.1	1.7	V
Dynamic o	haracteristics					
t _{rr}	reverse recovery time	$I_F = 1 A; V_R = 30 V;$ $dI_F/dt = 100 A/\mu s; T_j = 25 °C;$ see Figure 6	-	17.5	35	ns





2. Pinning information

Table 2.	Pinning	j information		
Pin	Symbol	Description	Simplified outline	Graphic symbol
1	К	cathode		
2	А	anode	mb	K — Ң A 001aaa020
mb	К	mounting base; cathode		
			SOD59 (TO-220AC)	

3. Ordering information

Table 3.Ordering information

Type number	Package		
	Name	Description	Version
BYV25F-600	TO-220AC	plastic single-ended package; heatsink mounted; 1 mounting hole; 2-lead TO-220AC	SOD59

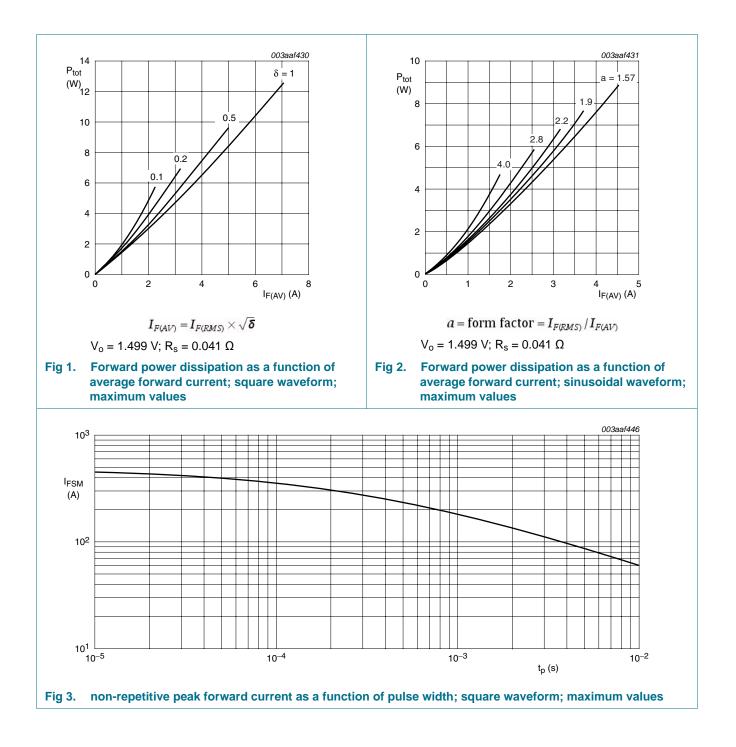
4. Limiting values

Table 4.Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
V _{RRM}	repetitive peak reverse voltage		-	600	V
V _{RWM}	crest working reverse voltage		-	600	V
V _R	reverse voltage	DC	-	600	V
I _{F(AV)}	average forward current	square-wave pulse; δ = 0.5 ; T _{mb} ≤ 126 °C; see <u>Figure 1;</u> see <u>Figure 2</u>	-	5	A
I _{FRM}	repetitive peak forward current	square-wave pulse; δ = 0.5 ; t _p = 25 µs; T _{mb} ≤ 126 °C	-	10	А
I _{FSM}	non-repetitive peak forward current	$t_p = 10 \text{ ms}$; sine-wave pulse; T _{j(init)} = 25 °C; see <u>Figure 3</u>	-	60	A
		t _p = 8.3 ms; sine-wave pulse; T _{j(init)} = 25 °C; see <u>Figure 3</u>	-	66	А
T _{stg}	storage temperature		-40	150	°C
Tj	junction temperature		-	150	°C

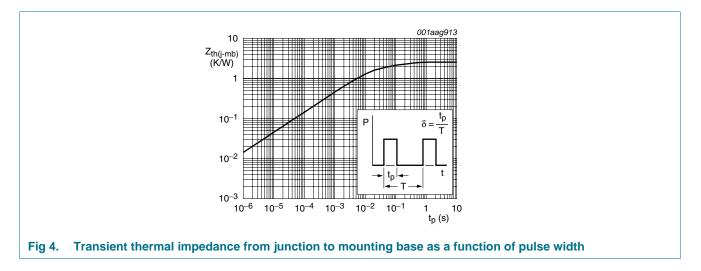
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5. Thermal characteristics

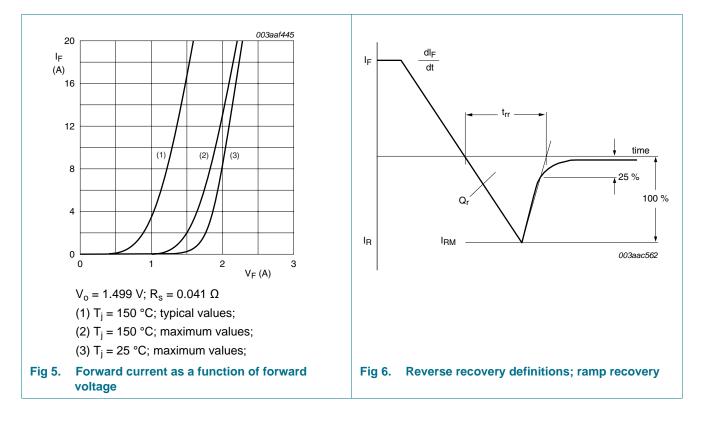
Table 5.	Thermal characteristics					
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
R _{th(j-mb)}	thermal resistance from junction to mounting base	see <u>Figure 4</u>	-	-	2.5	K/W
R _{th(j-a)}	thermal resistance from junction to ambient	in free air	-	60	-	K/W



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6. Characteristics

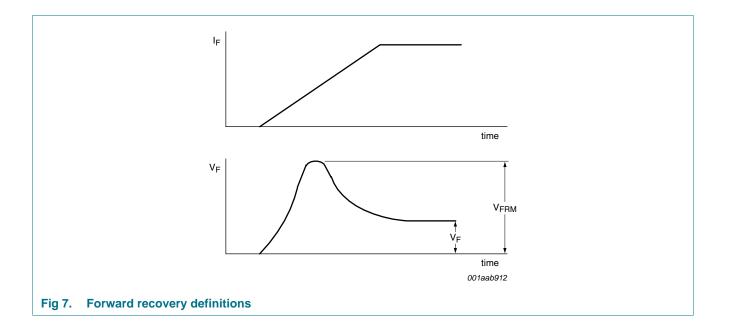
Characteristics					
Parameter	Conditions	Min	Тур	Max	Unit
aracteristics					
forward voltage	I _F = 5 A; T _j = 25 °C; see <u>Figure 5</u>	-	1.3	1.9	V
	I _F = 5 A; T _j = 150 °C; see <u>Figure 5</u>	-	1.1	1.7	V
reverse current	$V_{R} = 600 \text{ V}; \text{ T}_{j} = 100 ^{\circ}\text{C}$	-	-	1.5	mA
	$V_{R} = 600 \text{ V}; \text{ T}_{j} = 25 \text{ °C}$	-	-	50	μA
characteristics					
recovered charge	$I_F = 1 \text{ A}; V_R = 30 \text{ V}; dI_F/dt = 100 \text{ A}/\mu\text{s};$ $T_j = 25 \text{ °C}; \text{ see } \frac{\text{Figure 6}}{2}$	-	13	-	nC
reverse recovery time	$I_F = 1 \text{ A}; V_R = 30 \text{ V}; dI_F/dt = 100 \text{ A}/\mu\text{s};$ $T_j = 25 \text{ °C}; \text{ see } \frac{\text{Figure 6}}{2}$	-	17.5	35	ns
peak reverse recovery current	$I_F = 1 \text{ A}; V_R = 30 \text{ V}; dI_F/dt = 100 \text{ A}/\mu\text{s};$ $T_j = 25 \text{ °C}; \text{ see } \frac{\text{Figure 6}}{2}$	-	1.5	-	А
forward recovery voltage	$I_F = 1 \text{ A}; \text{ d}I_F/\text{d}t = 100 \text{ A}/\mu s; T_j = 25 \text{ °C};$ see Figure 7	-	3.2	-	V
	Parameter aracteristics forward voltage reverse current characteristics recovered charge reverse recovery time peak reverse recovery current forward recovery	$\begin{tabular}{ c c c c } \hline Parameter & Conditions \\ \hline \end{tabular} \hline \end{tabular} \hline \end{tabular} \\ \hline \end{tabular} aracteristics \\ \hline \end{tabular} forward voltage & I_F = 5 \end{tabular}, T_j = 25 \end{tabular} C; see Figure 5 \\ \hline \end{tabular} I_F = 5 \end{tabular}, T_j = 100 \end{tabular} C; see Figure 5 \\ \hline \end{tabular} reverse current & V_R = 600 \end{tabular}, T_j = 100 \end{tabular} C \\ \hline \end{tabular} V_R = 600 \end{tabular}, T_j = 100 \end{tabular} C \\ \hline \end{tabular} V_R = 600 \end{tabular}, T_j = 25 \end{tabular} C \\ \hline \end{tabular} characteristics \\ \hline \end{tabular} recovered charge & I_F = 1 \end{tabular}, V_R = 30 \end{tabular}, dI_F/dt = 100 \end{tabular} A/\mu s; \\ \hline \end{tabular} T_j = 25 \end{tabular} C; see Figure 6 \\ \hline \end{tabular} reverse recovery time & I_F = 1 \end{tabular}, V_R = 30 \end{tabular}, dI_F/dt = 100 \end{tabular} A/\mu s; \\ \hline \end{tabular} T_j = 25 \end{tabular} C; see Figure 6 \\ \hline \end{tabular} peak reverse recovery & I_F = 1 \end{tabular}, V_R = 30 \end{tabular}, dI_F/dt = 100 \end{tabular} A/\mu s; \\ \hline \end{tabular} T_j = 25 \end{tabular} C; see Figure 6 \\ \hline \end{tabular} forward recovery & I_F = 1 \end{tabular}, dI_F/dt = 100 \end{tabular} A/\mu s; \\ \hline \end{tabular} T_j = 25 \end{tabular} C; see Figure 6 \\ \hline \end{tabular} forward recovery & I_F = 1 \end{tabular}, dI_F/dt = 100 \end{tabular} A/\mu s; \\ \hline \end{tabular} T_j = 25 \end{tabular} C; see Figure 6 \\ \hline \end{tabular} forward recovery & I_F = 1 \end{tabular} A; dI_F/dt = 100 \end{tabular} A/\mu s; \\ \hline \end{tabular} T_j = 25 \end{tabular} C; see Figure 6 \\ \hline \end{tabular} forward recovery & I_F = 1 \end{tabular} A; dI_F/dt = 100 \end{tabular} A/\mu s; \\ \hline \end{tabular} T_j = 25 \end{tabular} C; see Figure 6 \\ \hline \end{tabular} forward recovery & I_F = 1 \end{tabular} A; dI_F/dt = 100 \end{tabular} A/\mu s; \\ \hline \end{tabular} T_j = 25 \end{tabular} C; see Figure 6 \\ \hline \end{tabular} forward recover \\ \hline \end{tabular} F_j = 25 \end{tabular} C; see Figure 6 \\ \hline \end{tabular} forward recover \\ \hline \end{tabular} F_j = 25 \end{tabular} C; $	$\begin{tabular}{ c c c c } \hline Parameter & Conditions & Min \\ \hline aracteristics & & & & & & & & & & & & & & & & & & &$	$\begin{array}{ c c c } \hline Parameter & Conditions & Min & Typ \\ \hline \mbox{aracteristics} & & & & & & & & & & \\ \hline \mbox{forward voltage} & I_F = 5 \mbox{ A; } T_j = 25 \ ^{\circ}\mbox{C; see Figure 5} & - & & 1.3 \\ \hline \mbox{I}_F = 5 \mbox{ A; } T_j = 150 \ ^{\circ}\mbox{C; see Figure 5} & - & & 1.1 \\ \hline \mbox{reverse current} & V_R = 600 \ V; \ T_j = 100 \ ^{\circ}\mbox{C} & - & & - \\ \hline \mbox{V}_R = 600 \ V; \ T_j = 25 \ ^{\circ}\mbox{C} & - & & - \\ \hline \mbox{V}_R = 600 \ V; \ T_j = 25 \ ^{\circ}\mbox{C} & - & & - \\ \hline \mbox{characteristics} & & & & & & & \\ \hline \mbox{characteristics} & & & & & & & & & \\ \hline \mbox{reverse recovery time} & I_F = 1 \ A; \ V_R = 30 \ V; \ dI_F/dt = 100 \ A/\mu s; \\ T_j = 25 \ ^{\circ}\mbox{C; see Figure 6} & & & & & & & & & & & \\ \hline \mbox{peak reverse recovery} & I_F = 1 \ A; \ V_R = 30 \ V; \ dI_F/dt = 100 \ A/\mu s; \\ T_j = 25 \ ^{\circ}\mbox{C; see Figure 6} & & & & & & & & & & & & & \\ \hline \mbox{peak reverse recovery} & I_F = 1 \ A; \ V_R = 30 \ V; \ dI_F/dt = 100 \ A/\mu s; \\ T_j = 25 \ ^{\circ}\mbox{C; see Figure 6} & & & & & & & & & & & & & & & & & & $	$\begin{array}{c c c c c c } \hline Parameter & Conditions & Min & Typ & Max \\ \hline \mbox{aracteristics} \\ \hline \mbox{forward voltage} & I_F = 5 \mbox{A}; \ T_j = 25 \ ^{\circ}C; \ see \ Figure 5 & - & 1.3 & 1.9 \\ \hline \ \ \ \ \ \ \ \ \ \ \ \ \ \ \ \ \ \$



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7. Package outline

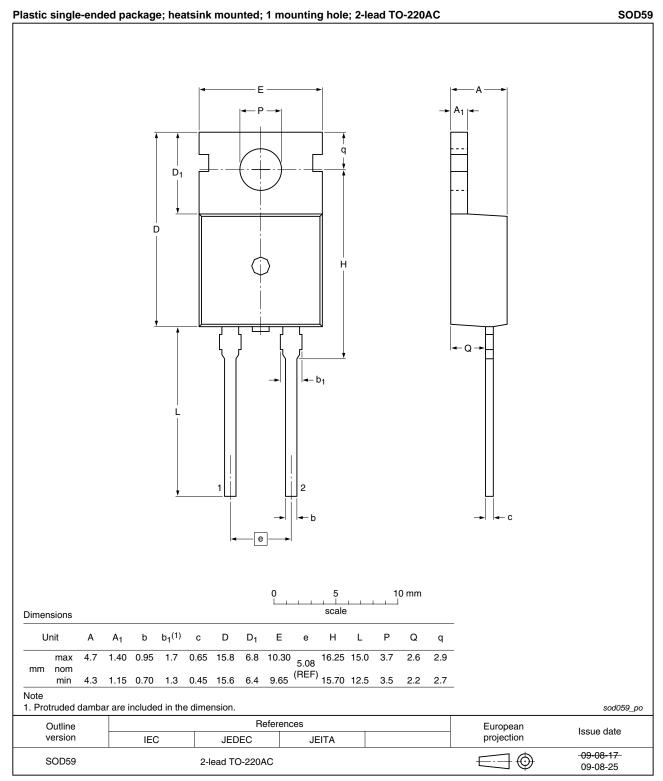


Fig 8.Package outline SOD59 (TO-220AC)

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BYV25F-600



8. Revision history

Table 7. Revision history					
Document ID	Release date	Data sheet status	Change notice	Supersedes	
BYV25F-600 v.1	20101001	Product data sheet	-	-	

9. Legal information

9.1 Data sheet status

Document status[1][2]	Product status ^[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

[1] Please consult the most recently issued document before initiating or completing a design.

[2] The term 'short data sheet' is explained in section "Definitions".

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